## ST 2SA539

## PNP Silicon Epitaxial Planar Transistor

for low frequency applications.

The transistor is subdivided into two groups, O and Y , according to its DC current gain.

Absolute Maximum Ratings $\left(\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}\right.$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector Base Voltage | $-\mathrm{V}_{\text {CBO }}$ | 60 | V |
| Collector Emitter Voltage | $-\mathrm{V}_{\text {CEO }}$ | 45 | V |
| Emitter Base Voltage | $-\mathrm{V}_{\text {EBO }}$ | 5 | V |
| Collector Current | $-\mathrm{I}_{\mathrm{C}}$ | 200 | mA |
| Power Dissipation | $\mathrm{P}_{\text {tot }}$ | 400 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| DC Current Gain <br> at $-\mathrm{V}_{\mathrm{CE}}=1 \mathrm{~V},-\mathrm{I}_{\mathrm{C}}=50 \mathrm{~mA}$ <br> Current Gain Group | $\begin{aligned} & \mathrm{h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{FE}} \end{aligned}$ | $\begin{gathered} 70 \\ 120 \end{gathered}$ | - | $\begin{aligned} & 140 \\ & 240 \end{aligned}$ | - |
| Collector Base Breakdown Voltage at $-\mathrm{I}_{\mathrm{C}}=100 \mu \mathrm{~A}$ | $-\mathrm{V}_{(\mathrm{BR}) \mathrm{CbO}}$ | 60 | - | - | V |
| Collector Emitter Breakdown Voltage $\text { at }-\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}$ | $-\mathrm{V}_{\text {(BR)CEO }}$ | 45 | - | - | V |
| Emitter Base Breakdown Voltage at $-I_{E}=10 \mu \mathrm{~A}$ | - $\mathrm{V}_{\text {(BR) }{ }^{\text {ebo }} \text { ( }}$ | 5 | - | - | V |
| Collector Base Cutoff Current at $-\mathrm{V}_{\mathrm{CB}}=45 \mathrm{~V}$ | $-\mathrm{I}_{\text {cво }}$ | - | - | 0.1 | $\mu \mathrm{A}$ |
| Emitter Base Cutoff Current at $-V_{E B}=3 \mathrm{~V}$ | $-l_{\text {ebo }}$ | - | - | 0.1 | $\mu \mathrm{A}$ |
| Collector Emitter Saturation Voltage at $-I_{C}=150 \mathrm{~mA},-\mathrm{I}_{\mathrm{B}}=15 \mathrm{~mA}$ | $-\mathrm{V}_{\text {CE(sat) }}$ | - | - | 0.5 | V |
| Base Emitter Saturation Voltage at $-I_{C}=150 \mathrm{~mA},-\mathrm{I}_{\mathrm{B}}=15 \mathrm{~mA}$ | $-\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ | - | - | 1.2 | V |
| Base Emitter on Voltage at $-\mathrm{V}_{\mathrm{CE}}=1 \mathrm{~V},-\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}$ | $-V_{B E(\text { on })}$ | 0.6 | - | 0.9 | V |
| Gain Bandwidth Product at $-\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V},-\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}$ | $\mathrm{f}_{\mathrm{T}}$ | 100 | - | - | MHz |
| Collector Output Capacitance at $-\mathrm{V}_{\mathrm{CB}}=10 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\text {ob }}$ | - | 6 | - | pF |

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$\mathrm{V}_{\mathrm{CE} \text { (sat) }}, \mathrm{V}_{\mathrm{BE} \text { (sat) }}-\mathrm{I}_{\mathrm{C}}$

$\mathrm{C}_{\mathrm{ob}}-\mathrm{V}_{\mathrm{CB}}$




